

MCP1700

Low Quiescent Current LDO

Features:

- 1.6 µA Typical Quiescent Current
- Input Operating Voltage Range: 2.3V to 6.0V
- Output Voltage Range: 1.2V to 5.0V
- 250 mA Output Current for Output Voltages ≥ 2.5V
- 200 mA Output Current for Output Voltages < 2.5V
- · Low Dropout (LDO) Voltage
 - 178 mV typical @ 250 mA for V_{OUT} = 2.8V
- 0.4% Typical Output Voltage Tolerance
- Standard Output Voltage Options:
 - 1.2V, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V, 5.0V
- Stable with 1.0 µF Ceramic Output Capacitor
- · Short Circuit Protection
- Overtemperature Protection

Applications:

- Battery-Powered Devices
- Battery-Powered Alarm Circuits
- · Smoke Detectors
- CO₂ Detectors
- · Pagers and Cellular Phones
- Smart Battery Packs
- Low Quiescent Current Voltage Reference
- PDAs
- Digital Cameras
- · Microcontroller Power

Related Literature:

- AN765, "Using Microchip's Micropower LDOs" (DS00765), Microchip Technology Inc., 2002
- AN766, "Pin-Compatible CMOS Upgrades to BiPolar LDOs" (DS00766), Microchip Technology Inc., 2002
- AN792, "A Method to Determine How Much Power a SOT23 Can Dissipate in an Application" (DS00792), Microchip Technology Inc., 2001

General Description:

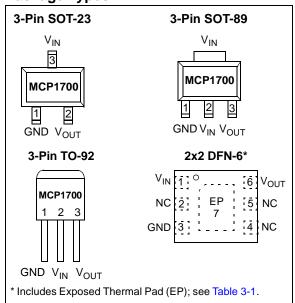
The MCP1700 is a family of CMOS low dropout (LDO) voltage regulators that can deliver up to 250 mA of current while consuming only 1.6 μ A of quiescent current (typical). The input operating range is specified from 2.3V to 6.0V, making it an ideal choice for two and three primary cell battery-powered applications, as well as single cell Li-lon-powered applications.

The MCP1700 is capable of delivering 250 mA with only 178 mV of input to output voltage differential (V_{OUT} = 2.8V). The output voltage tolerance of the MCP1700 is typically ±0.4% at +25°C and ±3% maximum over the operating junction temperature range of -40°C to +125°C.

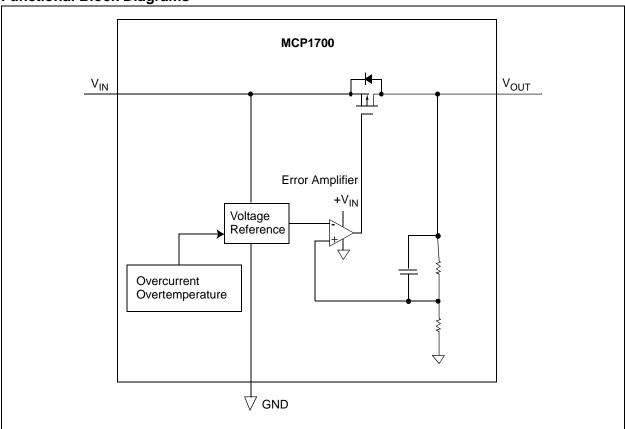
Output voltages available for the MCP1700 range from 1.2V to 5.0V. The LDO output is stable when using only 1 $\mu\text{F}~$ output capacitance. Ceramic, tantalum or aluminum electrolytic capacitors can all be used for input and output. Overcurrent limit and overtemperature shutdown provide a robust solution for any application.

Package options include SOT-23, SOT-89, TO-92 and 2x2 DFN-6.

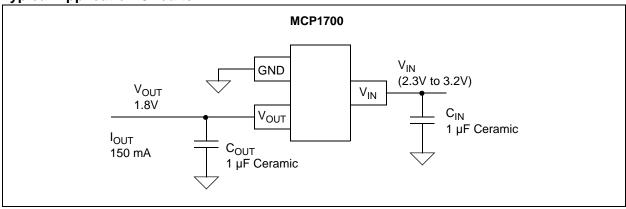
Package Types



Functional Block Diagrams



Typical Application Circuits



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

 † Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Characteristics: Unless otherwise specified, all limits are established for $V_{IN} = V_R + 1V$, $I_{LOAD} = 100 \ \mu A$, $C_{OUT} = 1 \ \mu F$ (X7R), $C_{IN} = 1 \ \mu F$ (X7R), $T_A = +25 \ C$.

Boldface type applies for junction temperatures, T_{.1} (Note 6) of -40°C to +125°C.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Input / Output Cha	racteristics					
Input Operating Voltage	V _{IN}	2.3	_	6.0	V	Note 1
Input Quiescent Current	Iq	_	1.6	4	μA	$I_L = 0 \text{ mA}, V_{IN} = V_R + 1V$
Maximum Output Current	I _{OUT_mA}	250 200	_ _	_ _	mA	For $V_R \ge 2.5V$ For $V_R < 2.5V$
Output Short Circuit Current	I _{OUT_SC}	_	408	_	mA	V _{IN} = V _R + 1V, V _{OUT} = GND Current (peak current) measured 10 ms after short is applied.
Output Voltage Regulation	V _{OUT}	V _R - 3.0% V _R - 2.0%	V _R ± 0.4%	V _R + 3.0% V _R + 2.0%	V	Note 2
V _{OUT} Temperature Coefficient	TCV _{OUT}	_	50	_	ppm/°C	Note 3
Line Regulation	ΔV _{OUT} / (V _{OUT} XΔV _{IN})	-1.0	±0.75	+1.0	%/V	$(V_R + 1)V \le V_{IN} \le 6V$
Load Regulation	ΔV _{OUT} /V _{OUT}	-1.5	±1.0	+1.5	%	$I_L=0.1$ mA to 250 mA for $V_R \geq 2.5 V$ $I_L=0.1$ mA to 200 mA for $V_R < 2.5 V$ Note 4
Dropout Voltage V _R > 2.5V	V _{IN} - V _{OUT}	_	178	350	mV	I _L = 250 mA, (Note 1, Note 5)
Dropout Voltage V _R < 2.5V	V _{IN} - V _{OUT}	_	150	350	mV	I _L = 200 mA, (Note 1, Note 5)
Output Rise Time	T _R	_	500	_	μs	10% V_R to 90% V_R V_{IN} = 0V to 6V, R_L = 50Ω resistive

- Note 1: The minimum V_{IN} must meet two conditions: $V_{IN} \ge 2.3 V$ and $V_{IN} \ge (V_R + 3.0\%) + V_{DROPOUT}$.
 - 2: V_R is the nominal regulator output voltage. For example: V_R = 1.2V, 1.5V, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V, 4.0V, 5.0V. The input voltage V_{IN} = V_R + 1.0V; I_{OUT} = 100 μ A.
 - 3: TCV_{OUT} = (V_{OUT-HIGH} V_{OUT-LOW}) *10⁶ / (V_R * ΔTemperature), V_{OUT-HIGH} = highest voltage measured over the temperature range. V_{OUT-LOW} = lowest voltage measured over the temperature range.
 - 4: Load regulation is measured at a constant junction temperature using low duty cycle pulse testing. Changes in output voltage due to heating effects are determined using thermal regulation specification TCV_{OUT}.
 - 5: Dropout voltage is defined as the input to output differential at which the output voltage drops 2% below its measured value with a V_R + 1V differential applied.
 - 6: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 150°C rating. Sustained junction temperatures above 150°C can impact the device reliability.
 - 7: The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired Junction temperature. The test time is small enough such that the rise in the Junction temperature over the ambient temperature is not significant.

DC CHARACTERISTICS (CONTINUED)

Electrical Characteristics: Unless otherwise specified, all limits are established for $V_{IN} = V_R + 1V$, $I_{LOAD} = 100 \mu A$, $C_{OUT} = 1 \mu F$ (X7R), $C_{IN} = 1 \mu F$ (X7R), $T_A = +25 ^{\circ}C$.

Boldface type applies for junction temperatures, T_J (Note 6) of -40°C to +125°C.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Output Noise	e _N	_	3	_	μV/(Hz) ^{1/2}	$I_L = 100 \text{ mA}, f = 1 \text{ kHz}, C_{OUT} = 1 \mu\text{F}$
Power Supply Ripple Rejection Ratio	PSRR	_	44	_	dB	$ f = 100 \text{ Hz}, C_{OUT} = 1 \mu\text{F}, I_L = 50 \text{ mA}, \\ V_{INAC} = 100 \text{ mV pk-pk}, C_{IN} = 0 \mu\text{F}, \\ V_R = 1.2 \text{V} $
Thermal Shutdown Protection	T _{SD}	_	140		°C	$V_{IN} = V_R + 1V, I_L = 100 \mu A$

- Note 1: The minimum V_{IN} must meet two conditions: $V_{IN} \ge 2.3V$ and $V_{IN} \ge (V_R + 3.0\%) + V_{DROPOUT}$.
 - 2: V_R is the nominal regulator output voltage. For example: $V_R = 1.2V$, 1.5V, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V, 4.0V, 5.0V. The input voltage $V_{IN} = V_R + 1.0V$; $I_{OUT} = 100 \ \mu A$.
 - 3: TCV_{OUT} = (V_{OUT-HIGH} V_{OUT-LOW}) *10⁶ / (V_R * ΔTemperature), V_{OUT-HIGH} = highest voltage measured over the temperature range. V_{OUT-LOW} = lowest voltage measured over the temperature range.
 - 4: Load regulation is measured at a constant junction temperature using low duty cycle pulse testing. Changes in output voltage due to heating effects are determined using thermal regulation specification TCV_{OUT}.
 - 5: Dropout voltage is defined as the input to output differential at which the output voltage drops 2% below its measured value with a V_R + 1V differential applied.
 - 6: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 150°C rating. Sustained junction temperatures above 150°C can impact the device reliability.
 - 7: The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired Junction temperature. The test time is small enough such that the rise in the Junction temperature over the ambient temperature is not significant.

TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise specified, all limits are established for $V_{IN} = V_R + 1V$, $I_{LOAD} = 100 \mu A$, $C_{OLIT} = 1 \mu F (X7R)$, $C_{IN} = 1 \mu F (X7R)$, $T_A = +25 ^{\circ}C$.

Boldface type applies for junction temperatures, T_J (Note 1) of -40°C to +125°C.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions		
Temperature Ranges								
Specified Temperature Range	T _A	-40		+125	°C			
Operating Temperature Range	TJ	-40		+125	°C			
Storage Temperature Range	T _A	-65		+150	°C			
Thermal Package Resistance	Thermal Package Resistance							
Thermal Resistance, 2x2 DFN	θ_{JA}	_	91	_	°C/W	EIA/JEDEC® JESD51-7		
	θ_{JC}	_	19	_	°C/W	FR-4 0.063 4-Layer Board		
Thermal Resistance, SOT-23	θ_{JA}	_	336	_	°C/W	EIA/JEDEC JESD51-7		
	θ_{JC}	_	110	_	°C/W	FR-4 0.063 4-Layer Board		
Thermal Resistance, SOT-89	θ_{JA}	_	180	_	°C/W	EIA/JEDEC JESD51-7		
	θ_{JC}	_	52	_	°C/W	FR-4 0.063 4-Layer Board		
Thermal Resistance, TO-92	θ_{JA}	_	160	_	°C/W			
	θ_{JC}	_	66.3	_	°C/W			

Note 1: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 150°C rating. Sustained junction temperatures above 150°C can impact the device reliability.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated: $V_R = 1.8V$, $C_{OUT} = 1~\mu F$ Ceramic (X7R), $C_{IN} = 1~\mu F$ Ceramic (X7R), $I_L = 100~\mu A$, $T_A = +25^{\circ}C$, $V_{IN} = V_R + 1V$.

Note: Junction Temperature (T_J) is approximated by soaking the device under test to an ambient temperature equal to the desired junction temperature. The test time is small enough such that the rise in Junction temperature over the Ambient temperature is not significant.

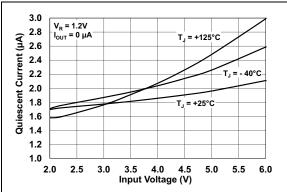


FIGURE 2-1: Input Quiescent Current vs. Input Voltage.

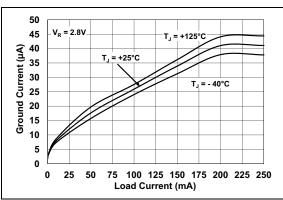


FIGURE 2-2: Ground Current vs. Load Current.

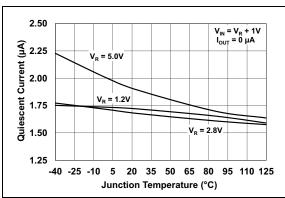


FIGURE 2-3: Quiescent Current vs. Junction Temperature.

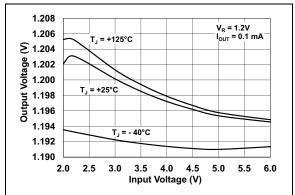


FIGURE 2-4: Output Voltage vs. Input Voltage $(V_R = 1.2V)$.

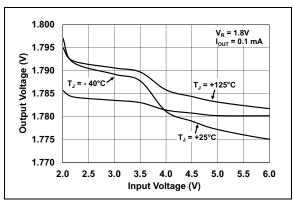


FIGURE 2-5: Output Voltage vs. Input Voltage $(V_R = 1.8V)$.

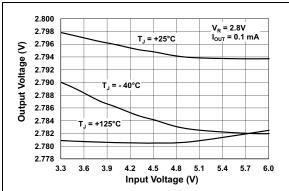


FIGURE 2-6: Output Voltage vs. Input Voltage $(V_R = 2.8V)$.

MCP1700

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = V_R + 1V.

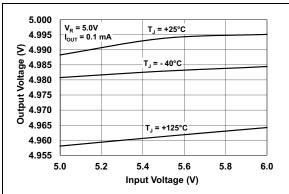


FIGURE 2-7: Output Voltage vs. Input Voltage ($V_R = 5.0V$).

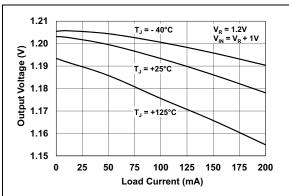


FIGURE 2-8: Output Voltage vs. Load Current ($V_R = 1.2V$).

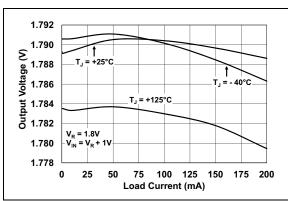


FIGURE 2-9: Output Voltage vs. Load Current ($V_R = 1.8V$).

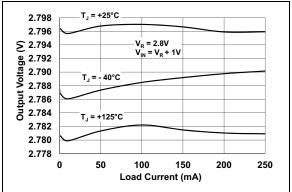


FIGURE 2-10: Output Voltage vs. Load Current ($V_R = 2.8V$).

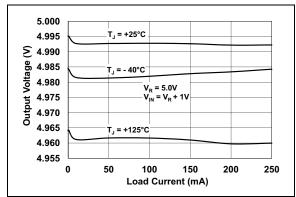


FIGURE 2-11: Output Voltage vs. Load Current ($V_R = 5.0V$).

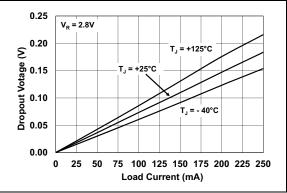


FIGURE 2-12: Dropout Voltage vs. Load Current ($V_R = 2.8V$).

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = V_R + 1V.

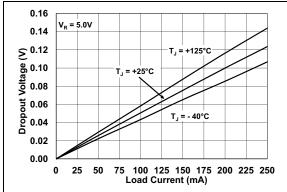


FIGURE 2-13: Dropout Voltage vs. Load Current ($V_R = 5.0V$).

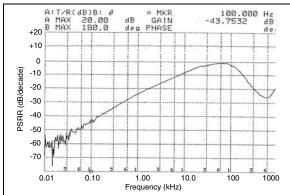


FIGURE 2-14: Power Supply Ripple Rejection vs. Frequency ($V_R = 1.2V$).

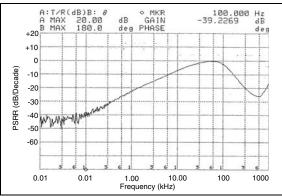


FIGURE 2-15: Power Supply Ripple Rejection vs. Frequency ($V_R = 2.8V$).

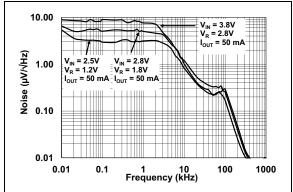


FIGURE 2-16: Noise vs. Frequency.

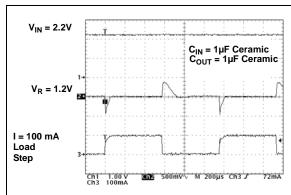


FIGURE 2-17: Dynamic Load Step $(V_R = 1.2V)$.

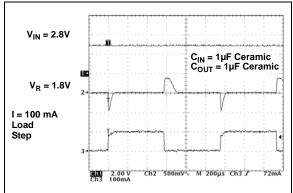


FIGURE 2-18: Dynamic Load Step $(V_R = 1.8V)$.

MCP1700

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = V_R + 1V.

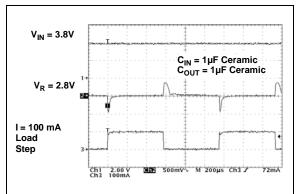


FIGURE 2-19: Dynamic Load Step $(V_R = 2.8V)$.

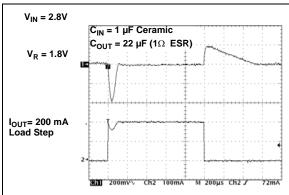


FIGURE 2-20: Dynamic Load Step $(V_R = 1.8V)$.

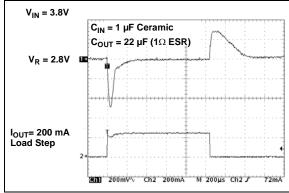


FIGURE 2-21: Dynamic Load Step $(V_R = 2.8V)$.

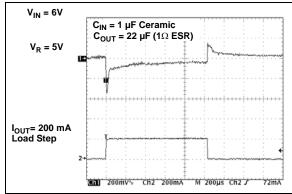


FIGURE 2-22: Dynamic Load Step $(V_R = 5.0V)$.

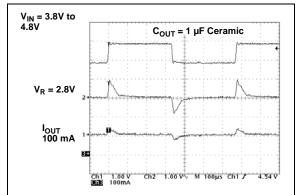


FIGURE 2-23: Dynamic Line Step $(V_R = 2.8V)$.

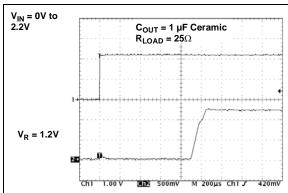


FIGURE 2-24: Start-up from V_{IN} ($V_R = 1.2V$).

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = V_R + 1V.

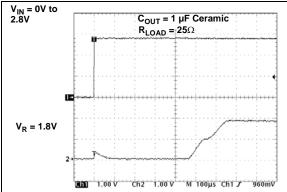


FIGURE 2-25: Start-up from V_{IN} $(V_R = 1.8V)$.

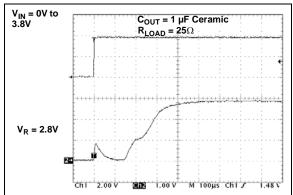


FIGURE 2-26: Start-up from V_{IN} ($V_R = 2.8V$).

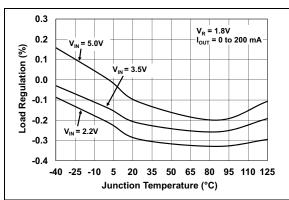


FIGURE 2-27: Load Regulation vs. Junction Temperature ($V_R = 1.8V$).

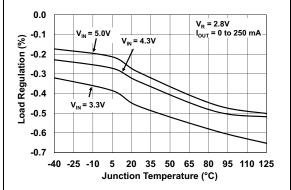


FIGURE 2-28: Load Regulation vs. Junction Temperature ($V_R = 2.8V$).

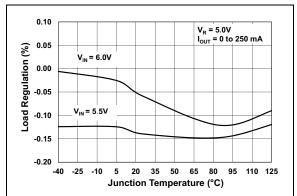


FIGURE 2-29: Load Regulation vs. Junction Temperature ($V_R = 5.0V$).

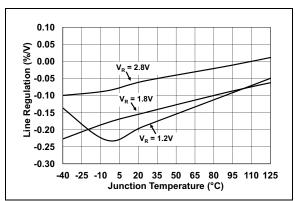


FIGURE 2-30: Line Regulation vs. Temperature ($V_R = 1.2V, 1.8V, 2.8V$).

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin No. SOT-23	Pin No. SOT-89	Pin No. TO-92	Pin No. 2x2 DFN-6	Name	Function
1	1	1	3	GND	Ground Terminal
2	3	3	6	V _{OUT}	Regulated Voltage Output
3	2	2	1	V _{IN}	Unregulated Supply Voltage
_	_	_	2, 4, 5	NC	No Connect
_	_	_	7	EP	Exposed Thermal Pad

3.1 Ground Terminal (GND)

Regulator ground. Tie GND to the negative side of the output and the negative side of the input capacitor. Only the LDO bias current (1.6 μ A typical) flows out of this pin; there is no high current. The LDO output regulation is referenced to this pin. Minimize voltage drops between this pin and the negative side of the load.

3.2 Regulated Output Voltage (VOLT)

Connect V_{OUT} to the positive side of the load and the positive terminal of the output capacitor. The positive side of the output capacitor should be physically located as close to the LDO V_{OUT} pin as is practical. The current flowing out of this pin is equal to the DC load current.

3.3 Unregulated Input Voltage Pin (V_{IN})

Connect V_{IN} to the input unregulated source voltage. As with all low dropout linear regulators, low source impedance is necessary for the stable operation of the LDO. The amount of capacitance required to ensure low source impedance will depend on the proximity of the input source capacitors or battery type. For most applications, 1 μ F of capacitance will ensure stable operation of the LDO circuit. For applications that have load currents below 100 mA, the input capacitance requirement can be lowered. The type of capacitor used can be ceramic, tantalum or aluminum electrolytic. The low ESR characteristics of the ceramic will yield better noise and PSRR performance at high frequency.

3.4 No Connect (NC)

No internal connection. The pins marked NC are true "No Connect" pins.

3.5 Exposed Thermal Pad (EP)

There is an internal electrical connection between the Exposed Thermal Pad (EP) and the GND pin; they must be connected to the same potential on the Printed Circuit Board (PCB).

4.0 DETAILED DESCRIPTION

4.1 Output Regulation

A portion of the LDO output voltage is fed back to the internal error amplifier and compared with the precision internal bandgap reference. The error amplifier output will adjust the amount of current that flows through the P-Channel pass transistor, thus regulating the output voltage to the desired value. Any changes in input voltage or output current will cause the error amplifier to respond and adjust the output voltage to the target voltage (refer to Figure 4-1).

4.2 Overcurrent

The MCP1700 internal circuitry monitors the amount of current flowing through the P-Channel pass transistor. In the event of a short circuit or excessive output current, the MCP1700 will turn off the P-Channel device for a short period, after which the LDO will attempt to restart. If the excessive current remains, the cycle will repeat itself.

4.3 Overtemperature

The internal power dissipation within the LDO is a function of input-to-output voltage differential and load current. If the power dissipation within the LDO is excessive, the internal junction temperature will rise above the typical shutdown threshold of 140°C. At that point, the LDO will shut down and begin to cool to the typical turn-on junction temperature of 130°C. If the power dissipation is low enough, the device will continue to cool and operate normally. If the power dissipation remains high, the thermal shutdown protection circuitry will again turn off the LDO, protecting it from catastrophic failure.

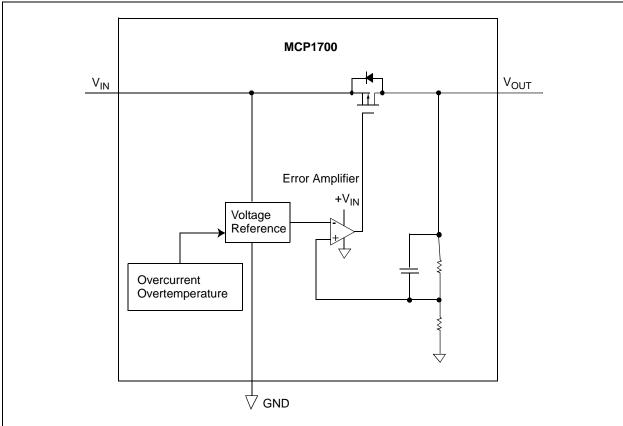


FIGURE 4-1: Block Diagram.

5.0 FUNCTIONAL DESCRIPTION

The MCP1700 CMOS low dropout linear regulator is intended for applications that need the lowest current consumption while maintaining output voltage regulation. The operating continuous load of the MCP1700 ranges from 0 mA to 250 mA (V $_{\rm R} \geq 2.5 {\rm V}$). The input operating voltage ranges from 2.3V to 6.0V, making it capable of operating from two, three or four alkaline cells or a single Li-lon cell battery input.

5.1 Input

The input of the MCP1700 is connected to the source of the P-Channel PMOS pass transistor. As with all LDO circuits, a relatively low source impedance (10 Ω) is needed to prevent the input impedance from causing the LDO to become unstable. The size and type of the required capacitor depend heavily on the input source type (battery, power supply) and the output current range of the application. For most applications (up to 100 mA), a 1 μ F ceramic capacitor will be sufficient to ensure circuit stability. Larger values can be used to improve circuit AC performance.

5.2 Output

The maximum rated continuous output current for the MCP1700 is 250 mA ($V_R \ge 2.5V$). For applications where $V_R < 2.5V$, the maximum output current is 200 mA.

A minimum output capacitance of 1.0 μ F is required for small signal stability in applications that have up to 250 mA output current capability. The capacitor type can be ceramic, tantalum or aluminum electrolytic. The ESR range on the output capacitor can range from 0Ω to 2.0Ω .

5.3 Output Rise time

When powering up the internal reference output, the typical output rise time of $500\,\mu s$ is controlled to prevent overshoot of the output voltage.

6.0 APPLICATION CIRCUITS AND ISSUES

6.1 Typical Application

The MCP1700 is most commonly used as a voltage regulator. Its low quiescent current and low dropout voltage make it ideal for many battery-powered applications.

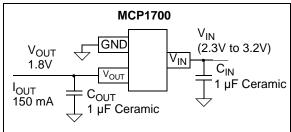


FIGURE 6-1:

Typical Application Circuit.

6.1.1 APPLICATION INPUT CONDITIONS

Package Type = SOT-23

Input Voltage Range = 2.3V to 3.2V

 V_{IN} maximum = 3.2V

 V_{OUT} typical = 1.8V

 $I_{OUT} = 150 \text{ mA maximum}$

6.2 Power Calculations

6.2.1 POWER DISSIPATION

The internal power dissipation of the MCP1700 is a function of input voltage, output voltage and output current. The power dissipation resulting from the quiescent current draw is so low it is insignificant (1.6 μ A x V_{IN}). The following equation can be used to calculate the internal power dissipation of the LDO.

EQUATION 6-1:

$$P_{LDO} = (V_{IN(MAX)} - V_{OUT(MIN)}) \times I_{OUT(MAX)}$$

P_{LDO} = Internal power dissipation of the

LDO Pass device

 $V_{IN(MAX)}$ = Maximum input voltage

V_{OUT(MIN)} = Minimum output voltage of the

LDO

The maximum continuous operating junction temperature specified for the MCP1700 is +125°C. To estimate the internal junction temperature of the MCP1700, the total internal power dissipation is multiplied by the thermal resistance from junction to ambient (R θ_{JA}). The thermal resistance from junction to ambient for the SOT-23 pin package is estimated at 230°C/W.

EQUATION 6-2:

$$T_{J(MAX)} = P_{TOTAL} \times R\theta_{JA} + T_{A(MAX)}$$

 $T_{J(MAX)}$ = Maximum continuous junction

temperature

P_{TOTAL} = Total power dissipation of the device

 $R\theta_{JA}$ = Thermal resistance from junction to

ambient

 $T_{A(MAX)}$ = Maximum ambient temperature

The maximum power dissipation capability for a package can be calculated given the junction-to-ambient thermal resistance and the maximum ambient temperature for the application. The following equation can be used to determine the maximum internal power dissipation of the package.

EQUATION 6-3:

$$P_{D(MAX)} = \frac{(T_{J(MAX)} - T_{A(MAX)})}{R\theta_{IA}}$$

 $P_{D(MAX)}$ = Maximum power dissipation of the

device

 $T_{J(MAX)}$ = Maximum continuous junction

temperature

 $T_{A(MAX)}$ = Maximum ambient temperature

 $R\theta_{JA}$ = Thermal resistance from junction to

ambient

EQUATION 6-4:

$$T_{J(RISE)} = P_{D(MAX)} \times R\theta_{JA}$$

 $T_{J(RISE)}$ = Rise in the device's junction

temperature over the ambient

temperature

P_{TOTAL} = Maximum power dissipation of the

device

 $R\theta_{JA}$ = Thermal resistance from junction to

ambient

EQUATION 6-5:

$$T_J = T_{J(RISE)} + T_A$$

 T_{J} = Junction Temperature

 $T_{J(RISE)}$ = Rise in the device's junction

temperature over the ambient

temperature

 T_A = Ambient temperature

6.3 Voltage Regulator

Internal power dissipation, junction temperature rise, junction temperature and maximum power dissipation are calculated in the following example. The power dissipation resulting from ground current is small enough to be neglected.

6.3.1 POWER DISSIPATION EXAMPLE

Package

Package Type = SOT-23

Input Voltage

 $V_{IN} = 2.3V \text{ to } 3.2V$

LDO Output Voltages and Currents

 $V_{OUT} = 1.8V$

 $I_{OUT} = 150 \text{ mA}$

Maximum Ambient Temperature

$$T_{A(MAX)} = +40^{\circ}C$$

Internal Power Dissipation

Internal Power dissipation is the product of the LDO output current times the voltage across the LDO (V_{IN} to V_{OLIT}).

 $P_{LDO(MAX)} = (V_{IN(MAX)} - V_{OUT(MIN)}) \times I_{OUT(MAX)}$

 $P_{LDO} = (3.2V - (0.97 \times 1.8V)) \times 150 \text{ mA}$

P_{LDO} = 218.1 milli-Watts

Device Junction Temperature Rise

The internal junction temperature rise is a function of internal power dissipation and the thermal resistance from junction to ambient for the application. The thermal resistance from junction to ambient $(R\theta_{IA})$ is derived from an EIA/JEDEC® standard for measuring thermal resistance for small surface mount packages. The EIA/ JEDEC specification is JESD51-7, "High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages". The standard describes the test method and board specifications for measuring the thermal resistance from junction to ambient. The actual thermal resistance for a particular application can vary depending on many factors, such as copper area and thickness. Refer to AN792, "A Method to Determine How Much Power a SOT-23 Can Dissipate in an Application" (DS00792), for more information regarding this subject.

 $T_{J(RISE)} = P_{TOTAL} \times R\theta_{JA}$

 $T_{J(RISE)} = 218.1 \text{ milli-Watts x } 230.0^{\circ}\text{C/Watt}$

 $T_{J(RISE)} = 50.2$ °C

Junction Temperature Estimate

To estimate the internal junction temperature, the calculated temperature rise is added to the ambient or offset temperature. For this example, the worst-case junction temperature is estimated below.

$$T_J = T_{J(RISE)} + T_{A(MAX)}$$

 $T_{.1} = 90.2$ °C

Maximum Package Power Dissipation at +40°C Ambient Temperature

 $2x2 DFN-6 (91°C/Watt = R\theta_{JA})$

 $P_{D(MAX)} = (125^{\circ}C - 40^{\circ}C) / 91^{\circ}C/W$

 $P_{D(MAX)} = 934 \text{ milli-Watts}$

SOT-23 (230.0°C/Watt = $R\theta_{JA}$)

 $P_{D(MAX)} = (125^{\circ}C - 40^{\circ}C) / 230^{\circ}C/W$

 $P_{D(MAX)} = 369.6 \text{ milli-Watts}$

SOT-89 (52°C/Watt = $R\theta_{JA}$)

 $P_{D(MAX)} = (125^{\circ}C - 40^{\circ}C) / 52^{\circ}C/W$

 $P_{D(MAX)} = 1.635 \text{ Watts}$

TO-92 (131.9°C/Watt = $R\theta_{JA}$)

 $P_{D(MAX)} = (125^{\circ}C - 40^{\circ}C) / 131.9^{\circ}C/W$

 $P_{D(MAX)} = 644 \text{ milli-Watts}$

6.4 Voltage Reference

The MCP1700 can be used not only as a regulator, but also as a low quiescent current voltage reference. In many microcontroller applications, the initial accuracy of the reference can be calibrated using production test equipment or by using a ratio measurement. When the initial accuracy is calibrated, the thermal stability and line regulation tolerance are the only errors introduced by the MCP1700 LDO. The low cost, low quiescent current and small ceramic output capacitor are all advantages when using the MCP1700 as a voltage reference.

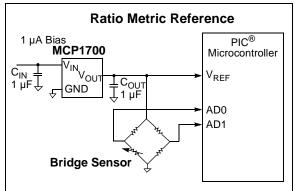


FIGURE 6-2: Using the MCP1700 as a voltage reference.

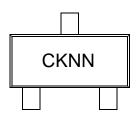
6.5 Pulsed Load Applications

For some applications, there are pulsed load current events that may exceed the specified 250 mA maximum specification of the MCP1700. The internal current limit of the MCP1700 will prevent high peak load demands from causing non-recoverable damage. The 250 mA rating is a maximum average continuous rating. As long as the average current does not exceed 250 mA, pulsed higher load currents can be applied to the MCP1700. The typical current limit for the MCP1700 is 550 mA ($T_A + 25^{\circ}$ C).

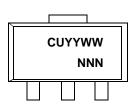
7.0 PACKAGING INFORMATION

7.1 Package Marking Information





3-Pin SOT-89

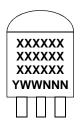


Symbol	Voltage *
CK	1.2
CM	1.8
CP	2.5
CQ	2.8
CR	3.0
CS	3.3
CU	5.0

Standard Extended Temp

* Custom output voltages available upon request. Contact your local Microchip sales office for more

3-Pin TO-92







6-Lead DFN (2x2x0.9 mm)



Part Number	Code
MCP1700T-1202E/MAY	ABB
MCP1700T-1802E/MAY	ABC
MCP1700T-2502E/MAY	ABD
MCP1700T-2802E/MAY	ABF
MCP1700T-3002E/MAY	ABE
MCP1700T-3302E/MAY	AAZ
MCP1700T-5002E/MAY	ABA

information.

Example



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

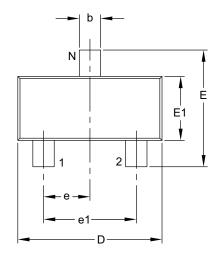
(e3) Pb-free JEDEC® designator for Matte Tin (Sn)

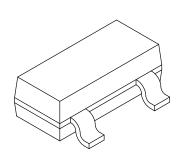
This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

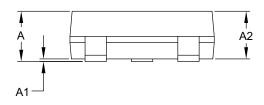
Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

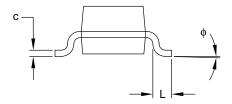
3-Lead Plastic Small Outline Transistor (TT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









	Units			MILLIMETERS			
D	imension Limits	MIN	NOM	MAX			
Number of Pins	N		3				
Lead Pitch	е		0.95 BSC				
Outside Lead Pitch	e1		1.90 BSC				
Overall Height	А	0.89	_	1.12			
Molded Package Thickness	A2	0.79	0.95	1.02			
Standoff	A1	0.01	-	0.10			
Overall Width	E	2.10	-	2.64			
Molded Package Width	E1	1.16	1.30	1.40			
Overall Length	D	2.67	2.90	3.05			
Foot Length	L	0.13	0.50	0.60			
Foot Angle	ф	0°	-	10°			
Lead Thickness	С	0.08	_	0.20			
Lead Width	b	0.30	_	0.54			

Notes:

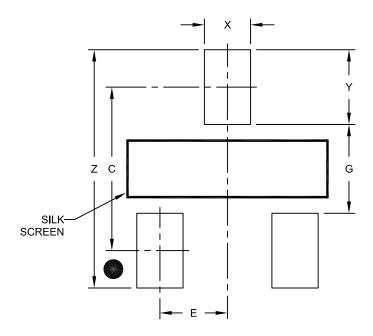
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.25 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-104B

3-Lead Plastic Small Outline Transistor (TT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX
Contact Pitch	Е		0.95 BSC	
Contact Pad Spacing	С		2.30	
Contact Pad Width (X3)	Х			0.65
Contact Pad Length (X3)	Υ			1.05
Distance Between Pads	G	1.25		
Overall Width	Z			3.35

Notes:

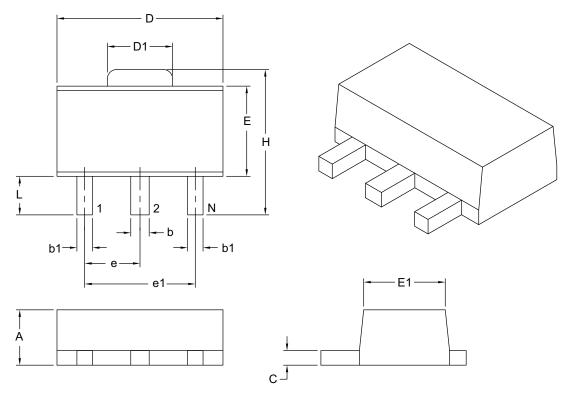
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2104A

3-Lead Plastic Small Outline Transistor Header (MB) [SOT-89]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units			
Dimen	sion Limits	MIN	MAX	
Number of Leads	N	N 3		
Pitch	е	1.50) BSC	
Outside Lead Pitch	e1	3.00) BSC	
Overall Height	Α	1.40	1.60	
Overall Width	Н	3.94	4.25	
Molded Package Width at Base	Е	2.29	2.60	
Molded Package Width at Top	E1	2.13	2.29	
Overall Length	D	4.39	4.60	
Tab Length	D1	1.40	1.83	
Foot Length	L	0.79	1.20	
Lead Thickness	С	0.35	0.44	
Lead 2 Width	b	0.41	0.56	
Leads 1 & 3 Width	b1	0.36	0.48	

Notes:

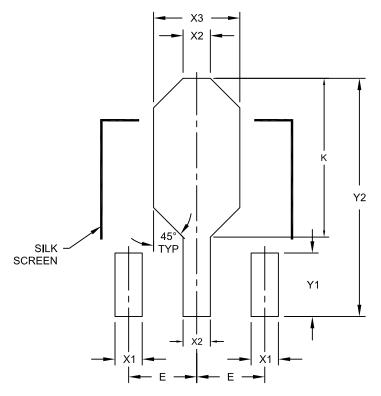
- 1. Dimensions D and E do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-029B

3-Lead Plastic Small Outline Transistor Header (MB) [SOT-89]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	MIN	NOM	MAX	
Contact Pitch	E		1.50 BSC	
Contact Pads 1 & 3 Width	X1			0.48
Contact Pad 2 Width	X2			0.56
Heat Slug Pad Width	X3			1.20
Contact Pads 1 & 3 Length	Y1		1.40	
Contact 2 Pad Length	Y2			4.25
-	K	2.60		2.85

Notes:

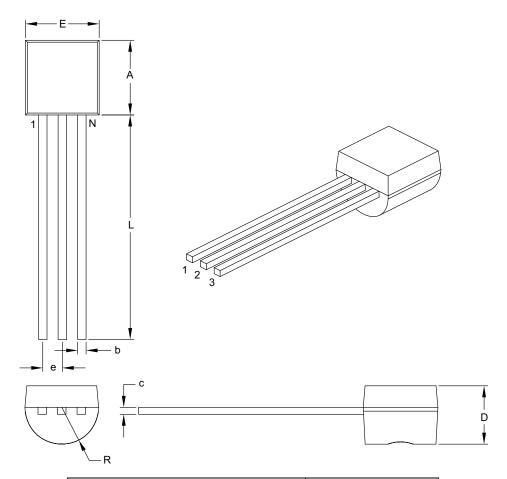
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2029A

3-Lead Plastic Transistor Outline (TO) [TO-92]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	INC	HES
Dimension	n Limits	MIN	MAX
Number of Pins	N	;	3
Pitch	е	.050	BSC
Bottom to Package Flat	D	.125	.165
Overall Width	Е	.175	.205
Overall Length	Α	.170	.210
Molded Package Radius	R	.080	.105
Tip to Seating Plane	L	.500	-
Lead Thickness	С	.014	.021
Lead Width	b	.014	.022

Notes:

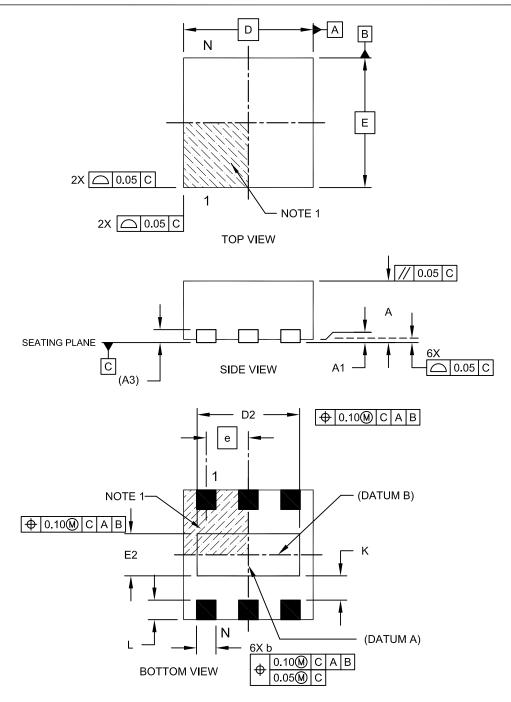
- 1. Dimensions A and E do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .005" per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-101B

6-Lead Plastic Dual Flat, No Lead Package (MA[Y]) - 2x2x0.9mm Body [DFN]

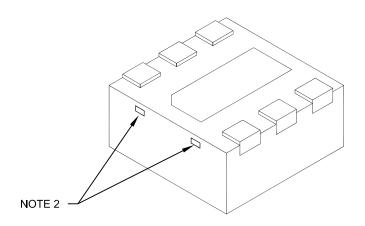
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-120C Sheet 1 of 2

6-Lead Plastic Dual Flat, No Lead Package (MA[Y]) - 2x2x0.9mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units			MILLIMETERS			
Dimension	Dimension Limits			MAX			
Number of Pins	N		6				
Pitch	е		0.65 BSC				
Overall Height	Α	0.80	0.85	0.90			
Standoff	A1	0.00	0.02	0.05			
Contact Thickness	A3	0.20 REF					
Overall Length	D	2.00 BSC					
Overall Width	Е	2.00 BSC					
Exposed Pad Length	D2	1.50	1.60	1.70			
Exposed Pad Width	E2	0.90	1.00	1.10			
Contact Width	b	0.25	0.30	0.35			
Contact Length	L	0.20	0.25	0.30			
Contact-to-Exposed Pad	K	0.20	-	-			

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package may have one or more exposed tie bars at ends.
- 3. Package is saw singulated.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-120C Sheet 2 of 2

M	C	P1	7	N	O
LVI				v	v

NOTES:

APPENDIX A: REVISION HISTORY

Revision C (October 2013)

The following is the list of modifications:

- Added new package to the family (2x2 DFN-6) and related information throughout the document.
- 2. Updated thermal package resistance information in Temperature Specifications.
- 3. Updated Section 3.0, Pin Descriptions.
- 4. Added package markings and drawings for the 2x2 DFN-6 package.
- 5. Added information related to the 2.8V option throughout the document.
- 6. Updated Product Identification System.
- 7. Minor typographical changes.

Revision B (February 2007)

- · Updated Packaging Information.
- Corrected Product Identification System.
- Changed X5R to X7R in Notes to DC Characteristics, Temperature Specifications, and Section 2.0, Typical Performance Curves.

Revision A (November 2005)

• Original Release of this Document.

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. X-	XXX X X /XX			
MCP1700 Tape & Reel	Voltage Tolerance Temp. Package Output Range			
Device:	MCP1700: Low Quiescent Current LDO			
Tape and Reel:	T: Tape and Reel only applies to SOT-23 and SOT-89 devices			
Standard Output Voltage: *	120 = 1.2V 180 = 1.8V 250 = 2.5V 280 = 2.8V 300 = 3.0V 330 = 3.3V 500 = 5.0V			
	* Custom output voltages available upon request. Contact your local Microchip sales office for more information			
Tolerance:	2 = 2%			
Temperature Range:	$E = -40^{\circ}C \text{ to } +125^{\circ}C \text{ (Extended)}$			
Package:	MAY = Plastic Small Outline Transistor (DFN), 6-lead MB = Plastic Small Outline Transistor (SOT-89), 3-lead TO = Plastic Small Outline Transistor (TO-92), 3-lead TT = Plastic Small Outline Transistor (SOT-23), 3-lead			

Examples:

2x2 DFN-6 Package:

- a) MCP1700T-1202E/MAY:1.2V V_{OUT}
- b) MCP1700T-1802E/MAY:1.8V V_{OUT}
- c) MCP1700T-2502E/MAY:2.5V V_{OUT}
- d) MCP1700T-2802E/MAY:2.8V V_{OUT}
- e) MCP1700T-3002E/MAY:3.0V V_{OUT}
- f) MCP1700T-3302E/MAY:3.3V V_{OUT}
- g) MCP1700T-5002E/MAY:5.0V V_{OUT}

SOT-89 Package:

- a) MCP1700T-1202E/MB:1.2V V_{OUT}
- b) MCP1700T-1802E/MB:1.8V V_{OUT}
- c) MCP1700T-2502E/MB:2.5V V_{OUT}
- d) MCP1700T-2802E/MB:2.8V V_{OUT}
- e) MCP1700T-3002E/MB:3.0V V_{OUT}
- f) MCP1700T-3302E/MB:3.3V V_{OUT}
- g) MCP1700T-5002E/MB:5.0V V_{OUT}

TO-92 Package:

- a) MCP1700-1202E/TO:1.2V V_{OUT}
- b) MCP1700-1802E/TO:1.8V V_{OUT}
- c) MCP1700-2502E/TO:2.5V V_{OUT}
- d) MCP1700-2802E/TO:2.8V V_{OUT}
- e) MCP1700-3002E/TO:3.0V V_{OUT}
- f) MCP1700-3302E/TO:3.3V V_{OUT}
- g) MCP1700-5002E/TO:5.0V V_{OUT}

SOT-23 Package:

- a) MCP1700T-1202E/TT:1.2V V_{OUT}
- b) MCP1700T-1802E/TT:1.8V V_{OUT}
- c) MCP1700T-2502E/TT:2.5V V_{OUT}
- d) MCP1700T-2802E/TT:2.8V V_{OUT}
- e) MCP1700T-3002E/TT:3.0V V_{OUT}
- f) MCP1700T-3302E/TT:3.3V V_{OUT}
- g) MCP1700T-5002E/TT:5.0V V_{OUT}

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the
 intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
 knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
 Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

QUALITY MANAGEMENT SYSTEM CERTIFIED BY DNV = ISO/TS 16949=

Trademarks

The Microchip name and logo, the Microchip logo, dsPIC, FlashFlex, KEELOQ, KEELOQ logo, MPLAB, PIC, PICmicro, PICSTART, PIC³² logo, rfPIC, SST, SST Logo, SuperFlash and UNI/O are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

FilterLab, Hampshire, HI-TECH C, Linear Active Thermistor, MTP, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Silicon Storage Technology is a registered trademark of Microchip Technology Inc. in other countries.

Analog-for-the-Digital Age, Application Maestro, BodyCom, chipKIT, chipKIT logo, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, dsSPEAK, ECAN, ECONOMONITOR, FanSense, HI-TIDE, In-Circuit Serial Programming, ICSP, Mindi, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, mTouch, Omniscient Code Generation, PICC, PICC-18, PICDEM, PICDEM.net, PICkit, PICtail, REAL ICE, rfLAB, Select Mode, SQI, Serial Quad I/O, Total Endurance, TSHARC, UniWinDriver, WiperLock, ZENA and Z-Scale are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

GestIC and ULPP are registered trademarks of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2005-2013, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

ISBN: 978-1-62077-526-4

Microchip received ISO/TS-16949:2009 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



Worldwide Sales and Service

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200

Fax: 480-792-7277 Technical Support:

http://www.microchip.com/

support

Web Address: www.microchip.com

Atlanta

Duluth, GA Tel: 678-957-9614

Fax: 678-957-1455

Boston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Cleveland

Independence, OH Tel: 216-447-0464 Fax: 216-447-0643

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Indianapolis

Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara

Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto

Mississauga, Ontario,

Canada

Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office

Suites 3707-14, 37th Floor Tower 6, The Gateway Harbour City, Kowloon Hong Kong

Tel: 852-2401-1200 Fax: 852-2401-3431

Australia - Sydney

Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing

Tel: 86-10-8569-7000 Fax: 86-10-8528-2104

China - Chengdu

Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Chongqing

Tel: 86-23-8980-9588 Fax: 86-23-8980-9500

China - Hangzhou

Tel: 86-571-2819-3187 Fax: 86-571-2819-3189

China - Hong Kong SAR

Tel: 852-2943-5100 Fax: 852-2401-3431

China - Nanjing

Tel: 86-25-8473-2460 Fax: 86-25-8473-2470

China - Qingdao

Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai

Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang

Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8864-2200 Fax: 86-755-8203-1760

China - Wuhan

Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian

Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

China - Xiamen

Tel: 86-592-2388138 Fax: 86-592-2388130

China - Zhuhai

Tel: 86-756-3210040 Fax: 86-756-3210049

ASIA/PACIFIC

India - Bangalore

Tel: 91-80-3090-4444 Fax: 91-80-3090-4123

India - New Delhi

Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune

Tel: 91-20-3019-1500

Japan - Osaka

Tel: 81-6-6152-7160 Fax: 81-6-6152-9310

Japan - Tokyo

Tel: 81-3-6880- 3770 Fax: 81-3-6880-3771

Korea - Daegu

Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul

Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Kuala Lumpur

Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

Malaysia - Penang

Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila

Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore

Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Hsin Chu

Tel: 886-3-5778-366 Fax: 886-3-5770-955

Taiwan - Kaohsiung

Tel: 886-7-213-7828 Fax: 886-7-330-9305

Taiwan - Taipei

Tel: 886-2-2508-8600 Fax: 886-2-2508-0102

Thailand - Bangkok Tel: 66-2-694-1351

Fax: 66-2-694-1350

EUROPE

Austria - Wels

Tel: 43-7242-2244-39 Fax: 43-7242-2244-393 Denmark - Copenhagen

Tel: 45-4450-2828

France - Paris

Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Munich

Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan

Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen Tel: 31-416-690399

Fax: 31-416-690340

Spain - Madrid

Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

UK - Wokingham Tel: 44-118-921-5869 Fax: 44-118-921-5820

08/20/13